

DYNAMIC CHARACTERISTICS (IGBT)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1\text{ MHz}$		1855		pF
C_{oes}	Output Capacitance			230		
C_{res}	Reverse Transfer Capacitance			110		
Q_g	Total Gate Charge ^③	Gate Charge $V_{GE} = 15V$ $V_{CC} = 0.5V_{CES}$ $I_C = I_{C2}$		170		nC
Q_{ge}	Gate-Emitter Charge			19		
Q_{gc}	Gate-Collector ("Miller") Charge			100		
$t_d(on)$	Turn-on Delay Time	Resistive Switching (25°C) $V_{GE} = 15V$ $V_{CC} = 0.8V_{CES}$ $I_C = I_{C2}$ $R_G = 10\Omega$		24		ns
t_r	Rise Time			85		
$t_d(off)$	Turn-off Delay Time			170		
t_f	Fall Time			125		
$t_d(on)$	Turn-on Delay Time	Inductive Switching (150°C) $V_{CLAMP(Peak)} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +150^\circ C$		25		ns
t_r	Rise Time			60		
$t_d(off)$	Turn-off Delay Time			210		
t_f	Fall Time			74		
E_{on}	Turn-on Switching Energy			2.8		mJ
E_{off}	Turn-off Switching Energy			2.8		
E_{ts}	Total Switching Losses			5.6		
$t_d(on)$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CLAMP(Peak)} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +25^\circ C$		27		ns
t_r	Rise Time			65		
$t_d(off)$	Turn-off Delay Time			190		
t_f	Fall Time			70		
E_{ts}	Total Switching Losses			5.2		mJ
g_{fe}	Forward Transconductance	$V_{CE} = 20V, I_C = 25A$	8.5	20		S

THERMAL AND MECHANICAL CHARACTERISTICS (IGBT and FRED)

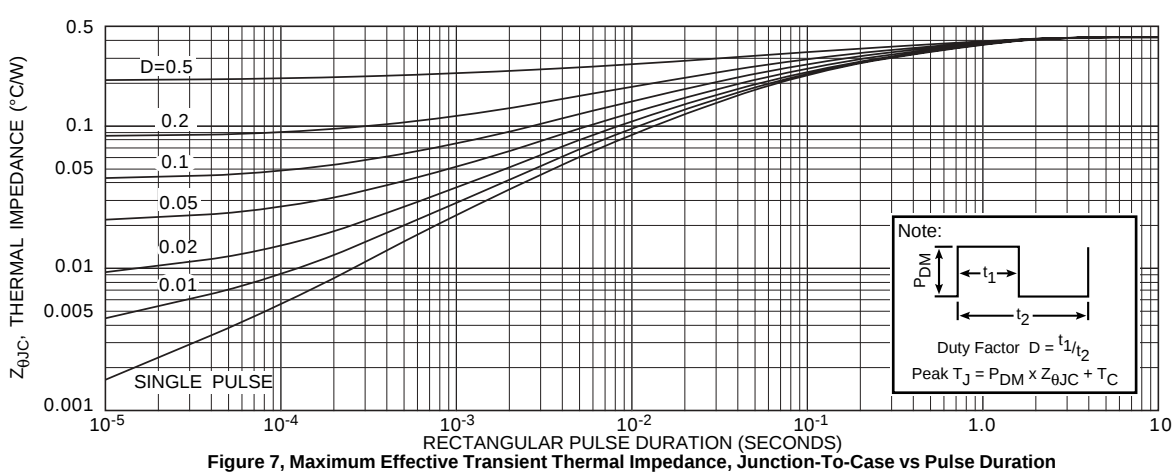
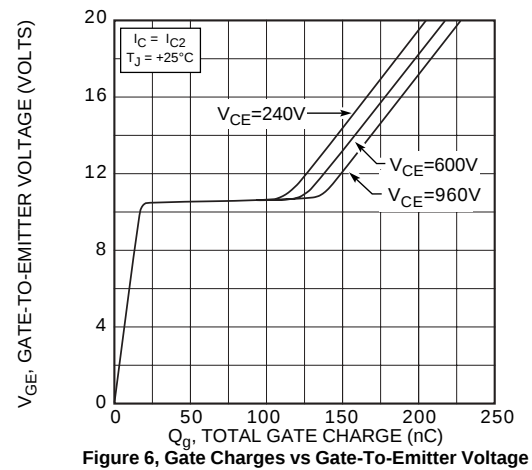
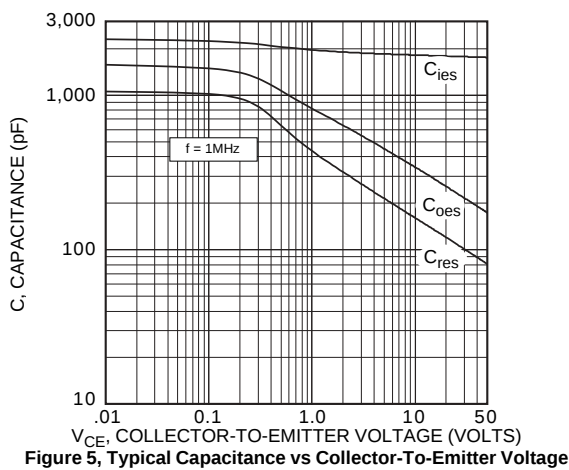
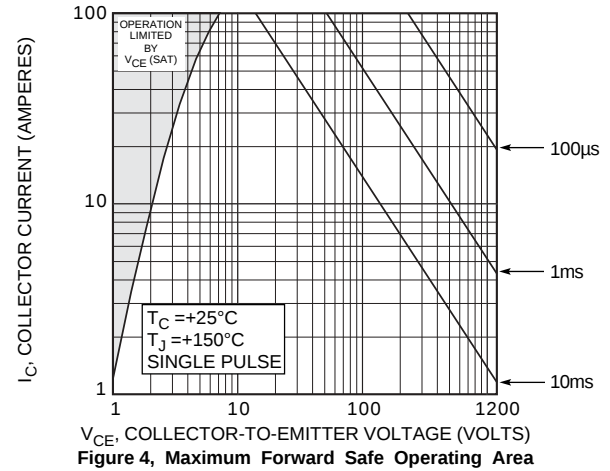
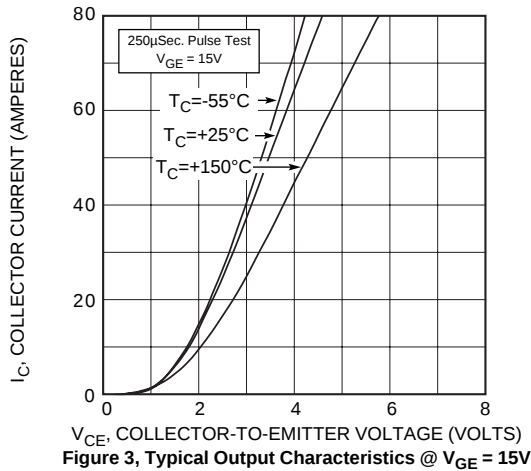
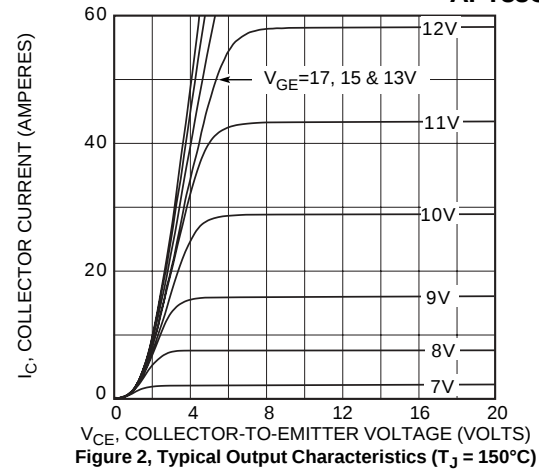
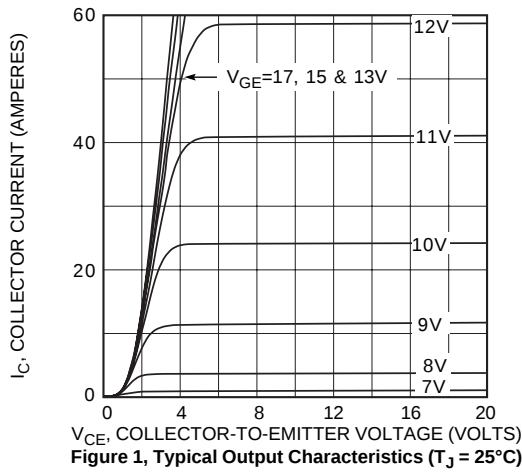
Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.42	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	
W_T	Package Weight		0.22		oz
			5.90		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② $I_C = I_{C2}$, $V_{CC} = 50V$, $R_{GE} = 25\Omega$, $L = 120\mu H$, $T_J = 25^\circ C$

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.



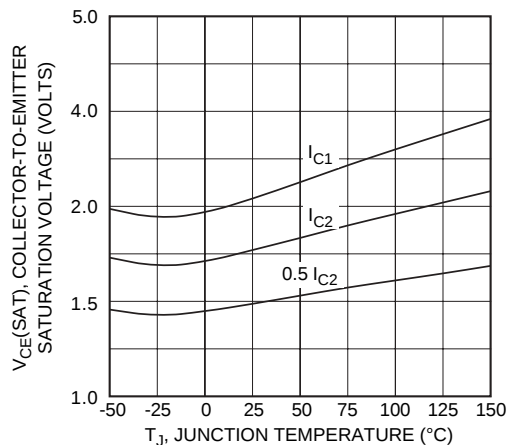
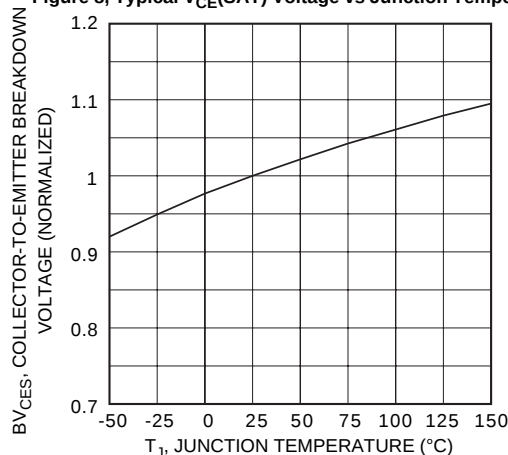
Figure 8, Typical $V_{CE(SAT)}$ Voltage vs Junction Temperature

Figure 10, Breakdown Voltage vs Junction Temperature

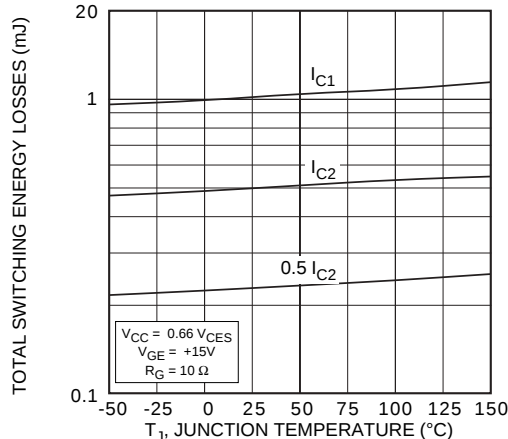


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

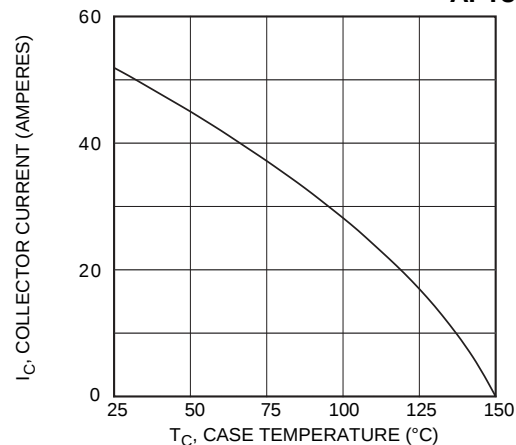


Figure 9, Maximum Collector Current vs Case Temperature

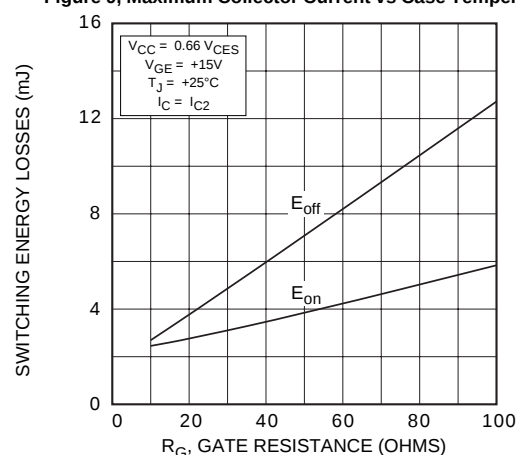


Figure 11, Typical Switching Energy Losses vs Gate Resistance

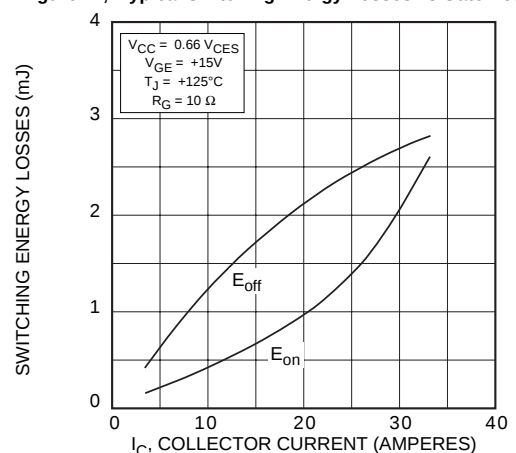


Figure 13, Typical Switching Energy Losses vs Collector Current

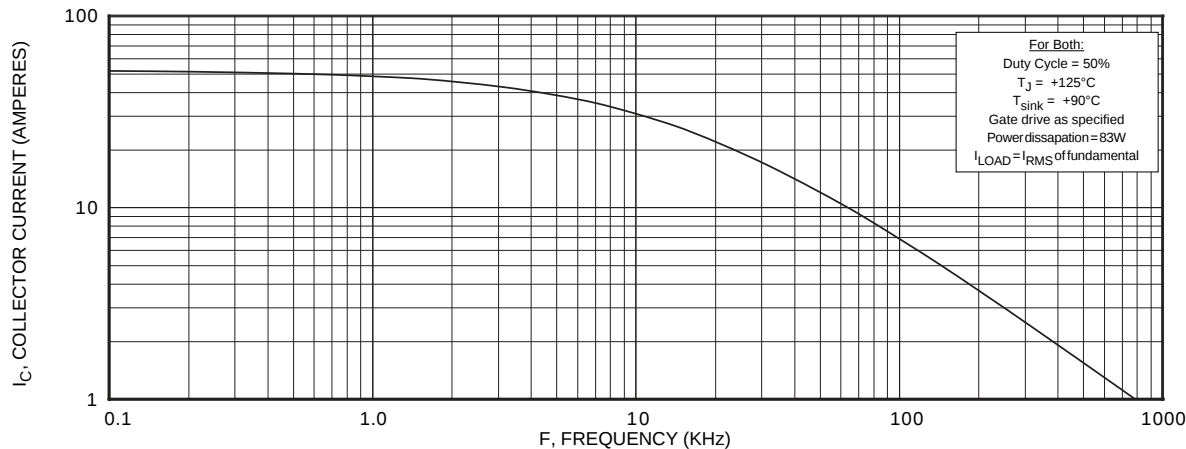


Figure 14, Typical Load Current vs Frequency

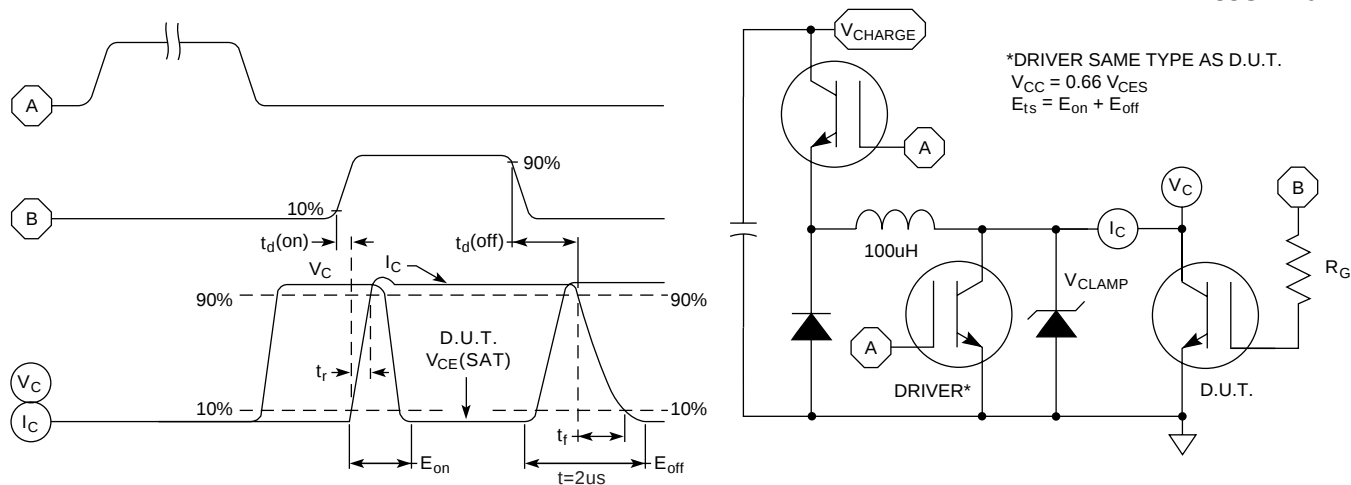


Figure 15, Switching Loss Test Circuit and Waveforms

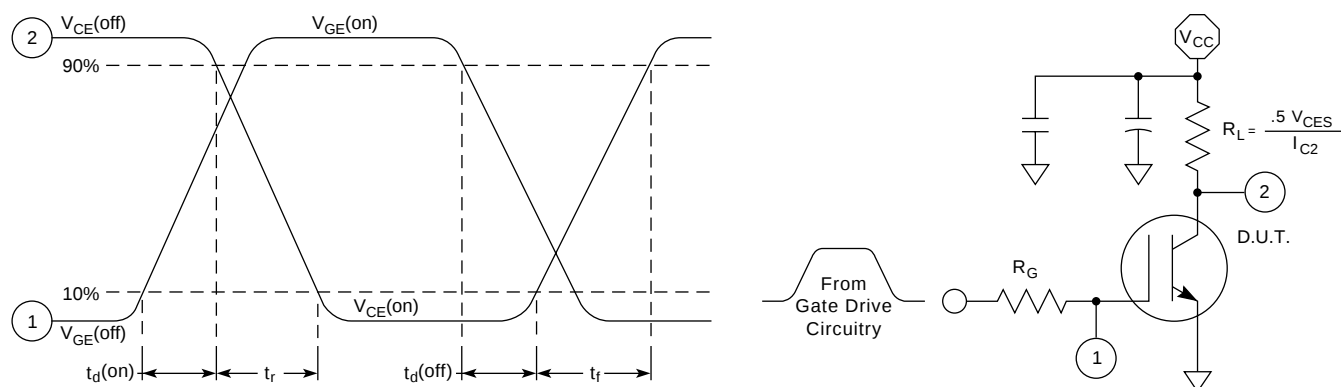


Figure 16, Resistive Switching Time Test Circuit and Waveforms

T0-247 Package Outline

